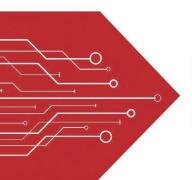
MSKSEMI















ESD

TVS

TSS

MOV

GDT

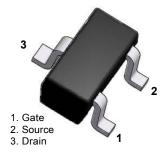
PLED

Broduct data sheet



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{DS}	Drain-Source Voltage	30	V	
V _{GS}	Continuous Gate-Source Voltage	±20V	V	
I _D	Continuous Drain Current	100	mA	
P _D	Power Dissipation	150	mW	
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	°C /W	
T _{STG}	Storage Temperature Range	-55 to +150	°C	
TJ	Operating Junction Temperature	+150	°C	



SOT-523

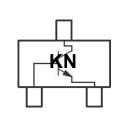
Specification Features:

- Low On-resistance
- Fast Switching Speed
- Low Voltage Drive Makes This Device Ideal for Portable Equipment
- Easily Designed Drive Circuits
- Easy to Parallel
- RoHS Compliant & Green EMC
- Matte Tin(Sn) Lead Finish
- Weight: approx. 0.002g

Electrical Symbol:

O Drain Gate 常 Gate Protection Diode

Device Marking Code:



These ratings are limiting values above which the serviceability of the device may be impaired.







Off Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
			Min	Тур	Max	Uill
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =10uA	30			Volts
I _{GSS}	Gate-Body Leakage	V_{DS} =0V, V_{GS} = $\pm 20V$			±1	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V			1	μA

On Characteristics

Symbol	Parameter	Test Condition	Limits			Unit
			Min	Тур	Max	Oill
$V_{th(GS)}$	Gate-Threshold Voltage	V _{DS} = 3V, I _D =100uA	0.8		1.5	Volts
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =4V, I _D =10mA			8	Ω
		V _{GS} =2.5V, I _D =1mA			13	Ω
g fs	Forward Trans Conductance	V _{DS} =3V, I _D =10mA	20			ms
V _{SD}	Drain-Source Diode Forward Voltage	I _S =115mA, V _{GS} =0V			1.2	V

Dynamic Characteristics

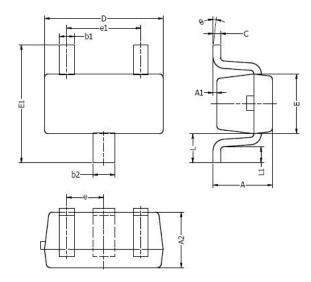
Symbol	Parameter	Test Condition	Limits			Unit
		rest Condition	Min	Тур	Max	Unit
Ciss	Input Capacitance	V _{DS} = 5V		13		pF
Coss	Output Capacitance	V _{GS} = 0V		9		рF
Crss	Reverse Transfer Capacitance	f = 1.0MHz		4		pF

Switching Characteristics

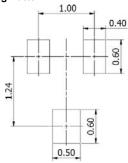
Symbol	Parameter	Test Condition	Limits			llmit
			Min	Тур	Max	Unit
t _{D(on)}	Furn-on Time $V_{DD}=5V, R_L=500\Omega,$			15		nS
t _{D(off)}	Turn-off Time	I_D =10mA, V_{Gs} =5V, R_G = 10 Ω		80		nS



SOT-523 Package Outline



Typical Soldering Pattern:



DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	0.70	0.90	0.028	0.035	
A1	0.00	0.10	0.000	0.004	
A2	0.70	0.80	0.028	0.031	
b1	0.15	0.25	0.006	0.010	
b2	0.25	0.35	0.010	0.014	
С	0.10	0.20	0.004	0.008	
D	1.50	1.70	0.059	0.067	
E	0.70	0.90	0.028	0.035	
E1	1.45	1.75	0.057	0.069	
е	0.50 TYP.		0.020 TYP.		
e1	0.90	1.10	0.035	0.043	
L	0.40 REF.		0.016	REF.	
L1	0.10	0.30	0.004	0.012	
θ	O °	8 °	O °	8 °	

NOTES:

- Above package outline conforms to JEITA EAIJ ED-7500A SC-75A.
 Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.



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